

# Lattice Constant of Sr-doped Lanthanum Titanate Thin Films with Various Oxygen Contents

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## ABSTRACT

In this study, Sr-doped  $\text{LaTiO}_3(\text{Sr}_{0.16}\text{La}_{0.84}\text{TiO}_3)$  thin films on  $\text{SrTiO}_3(001)$  were fabricated by the RF magnetron sputtering system. The deposited Sr-doped lanthanum titanate films were annealed under different oxygen pressure ( $10^{-4}$  torr,  $6 \times 10^{-5}$  torr,  $4 \times 10^{-5}$  torr, and  $< 2 \times 10^{-5}$  torr). Using X-ray  $\theta$ - $2\theta$  scan, the c-axis lengths of the films with different oxygen contents were investigated. Using X-ray asymmetry scans, the a-axis and b-axis of the films were investigated. Comparison between the calculated lattice constants of the films and the lattice constants of bulk materials will be discussed. Finally, we study the stress between substrates and films grown in different oxygen pressure by investigating the strains dependence of  $\sin^2 \psi$ .

Keywords :  $\text{Sr}_{0.16}\text{La}_{0.84}\text{TiO}_3$ 、lattice constant、epitaxial growth、oxygen content

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## REFERENCES

- [1]S. Leoni, L. Craco, A. Ormeci, and H. Rosner, Solid State Sciences 8, 1138-1143 (2006) [2]Masatoshi Imada, Atsushi Fulimori, Yoshinori Tokura, Rev. Mod. Phys., 70, 1059 (2008) [3] Franklin J. Wong, Seung-Hyub Baek, Rajesh V. Chopdekar, Virat V. Mehta, Ho-Won Jang, Chang-Beom Eom, and Yuri Suzuki, Phys. Rev. B 81, 161101(R) (2010) [4]Joseph E. Sunstrom IV, Susan M. Kauzlarich, and Peter Klavins, Chem. Mater. 4, 346-353(1992) [5] S. A. Howard, J. K. Yau, and H.U. Anderson, J. Appl. Phys. 65 (1989) [6]S. L. Yan, L Fang, M. S. Si, H.L. Cao, Q.X. Song, J Yan, X.D. Zhou, J.M. Hao Supercond. Sci. Technol 7, 681 - 684 (1994) [7]Bing H. Hwang, S.Y. Chiou, Thin Solid Films 304, 286-293 (1997) [8]Lamartine Meda, Klaus H. Dahmen, Saaleh Hayek, Hamid Garmestani, Journal of Crystal Growth 263, 185 (2004) [9]林政學, "應力對鈦酸鋇/鋁薄膜之傳輸特性研究",大葉大學碩士論文,2010 [10]蔡俊璋, "鈦酸鋇薄膜成長於不同基座之X光θ-2θ及應變研究",大葉大學碩士論文,2011 [11]吳翼胎, "儀中心簡訊",第十三卷第六期,1992 [12]許樹恩、吳泰伯, "X光繞射原理與材料結構分析",中國材料科學學會 [13]B. D. Cullity, S. R. Stock, "Elements of X-ray diffraction" Pearson Prentice Hall, (2001) [14]許樹恩、吳泰伯, "X光繞射原理與材料結構分析",中國材料科學學會 [15]B. D. Cullity, S. R. Stock, "Elements of X-ray diffraction" Pearson Prentice Hall, (2001) [16]美國國家標準和技術院(National Institute for Standards and Technology, NIST) [17]A.Ohtomo, D.A.Muller, J. L. Grazul, and H. Y. Hwang, Appl. Phys. Lett. 80, 3922 (2002) [18] Masahito Mochizuki, Masatoshi Imada, New Journal of Physics 6, 154 (2004) [19]S. Liang, D.J. Wang, J.R. Sun, and B.G. Shen, Solid State Communication 148, 386 (2008) [20]黃晨益, "含氧量對鈦酸鋇摻鋁薄膜之傳輸特性研究",大葉大學碩士論文,2013